

SILICON MOS N-CHANNEL RF POWER TRANSISTOR

150 W, up to 30 MHz, Enhancement Mode

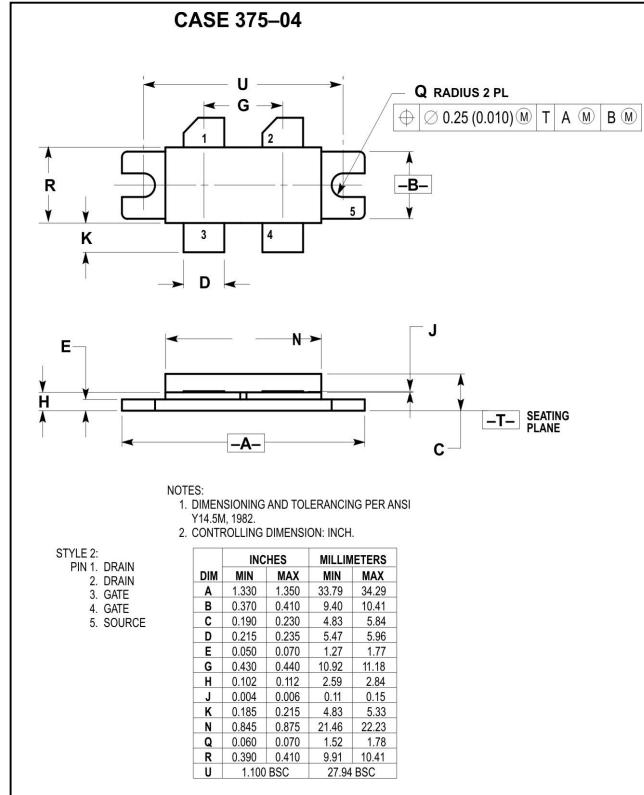
MRF141G

The silicon MOS transistor is designed for professional transmitter applications in the HF frequency range.

- Guaranteed Performance at 175 MHz, 28 V:
- Output Power: 150 W
- Power Gain 12 dB
- Efficiency: 45 %

Absolute Maximum Ratings

Parameters	Sym	Value	Unit
Drain-Source Voltage	V _{DSS}	65	V _{DC}
Drain Current-Continuous	I _D	16	A _{DC}
Gate-Source Voltage	V _{GS}	±40	V _{DC}
Storage Temperature Range	T _{STG}	-65 tu +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	0.35	°C/W
Total Power Dissipation @T _C =25 °C	P _D	500	W



Parameters

Parameter	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage (I _D =100.0 mA, V _{GS} =0 V)	V _{(BR)DSS}	65	—	—	V _{DC}
Gate-Source Leakage Current (V _{GS} =20 V, V _{DS} =0 V)	I _{GSS}	—	—	1.0	μA _{DC}
Zero Gate Voltage Drain Leakage Current (V _{DS} = 28 V, V _{GS} =0 V)	I _{DSS}	—	—	5.0	mA _{DC}
Gate Threshold Voltage (V _{DS} = 10 V, I _D = 100 mA)	V _{GS(TH)}	1.0	—	5.0	V _{DC}
Forward Transconductance (V _{DS} = 10 V, I _D = 5.0 A)	G _{FS}	5.0	7.0	—	mhos
Input Capacitance (V _{DS} = 28 V, V _{GS} =0 V, f = 1 MHz)	C _{ISS}	—	450	—	pF
Output Capacitance (V _{DS} = 28 V, V _{GS} =0 V, f = 1 MHz)	C _{OSS}	—	320	—	pF
Reverse Transfer Capacitance (V _{DS} = 28 V, V _{GS} =0 V, f = 1 MHz)	C _{RSS}	—	35	—	pF
Power Gain (f = 175 MHz, V _{DD} = 28 V, P _{OUT} =300 W, I _{DQ} = 500 mA)	G _p	12	14	—	dB
Drain Efficiency (f = 175 MHz, V _{DD} = 28 V, P _{OUT} =300 W, I _{DQ} = 500 mA)	η _D	45	55	—	%

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Specification is subject to change without notice